



Welcome to [E-XFL.COM](https://www.e-xfl.com)

### Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

### Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	36864
Number of I/O	97
Number of Gates	125000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	144-LBGA
Supplier Device Package	144-FPBGA (13x13)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/microchip-technology/a3p125-1fg144">https://www.e-xfl.com/product-detail/microchip-technology/a3p125-1fg144</a>

ProASIC3 Devices	A3P015 <sup>1</sup>	A3P030	A3P060	A3P125	A3P250	A3P400	A3P600	A3P1000
Cortex-M1 Devices <sup>2</sup>					M1A3P250	M1A3P400	M1A3P600	M1A3P1000
Package Pins								
QFN	QN68	QN48, QN68, QN132 <sup>7</sup>	QN132 <sup>7</sup>	QN132 <sup>7</sup>	QN132 <sup>7</sup>			
CS			CS121	VQ100	VQ100			
VQFP		VQ100	VQ100	TQ144	VQ100			
TQFP			TQ144	PQ208	PQ208	PQ208	PQ208	PQ208
PQFP			FG144	FG144	FG144/256 <sup>5</sup>	FG144/256/ 484	FG144/256/ 484	FG144/256/ 484
FBGA								

**Notes:**

1. A3P015 is not recommended for new designs.
2. Refer to the [Cortex-M1](#) product brief for more information.
3. AES is not available for Cortex-M1 ProASIC3 devices.
4. Six chip (main) and three quadrant global networks are available for A3P060 and above.
5. The M1A3P250 device does not support this package.
6. For higher densities and support of additional features, refer to the [ProASIC3E Flash Family FPGAs](#) datasheet.
7. Package not available.

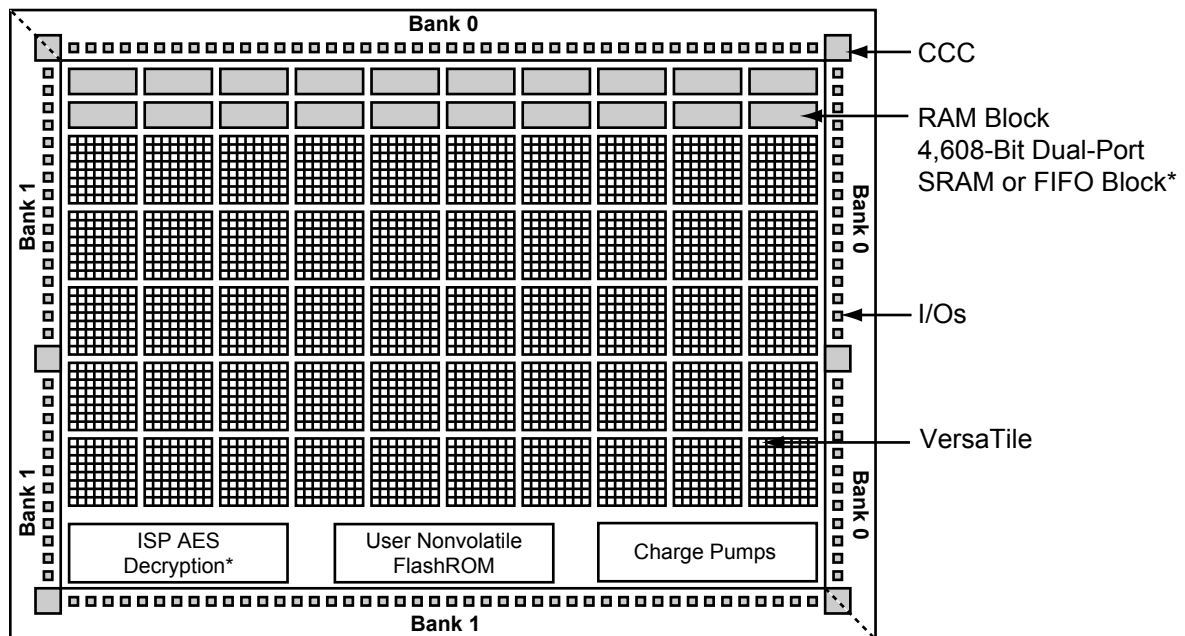
## Advanced Flash Technology

The ProASIC3 family offers many benefits, including nonvolatility and reprogrammability through an advanced flash-based, 130-nm LVC MOS process with seven layers of metal. Standard CMOS design techniques are used to implement logic and control functions. The combination of fine granularity, enhanced flexible routing resources, and abundant flash switches allows for very high logic utilization without compromising device routability or performance. Logic functions within the device are interconnected through a four-level routing hierarchy.

## Advanced Architecture

The proprietary ProASIC3 architecture provides granularity comparable to standard-cell ASICs. The ProASIC3 device consists of five distinct and programmable architectural features (Figure 1-1 and Figure 1-2 on page 1-4):

- FPGA VersaTiles
- Dedicated FlashROM
- Dedicated SRAM/FIFO memory<sup>†</sup>
- Extensive CCCs and PLLs<sup>†</sup>
- Advanced I/O structure



**Note:** \*Not supported by A3P015 and A3P030 devices

**Figure 1-1 • ProASIC3 Device Architecture Overview with Two I/O Banks (A3P015, A3P030, A3P060, and A3P125)**

<sup>†</sup> The A3P015 and A3P030 do not support PLL or SRAM.

0 – I/O is set to drive out logic Low

Last Known State – I/O is set to the last value that was driven out prior to entering the programming mode, and then held at that value during programming

Z -Tristate: I/O is tristated

The window titled "Specify I/O States During Programming" contains a table with the following data:

	Port Name	Macro Cell	Pin Number	I/O State (Output Only)
	BIST	ADLIB:INBUF	T2	1
	BYPASS_ID	ADLIB:INBUF	K1	1
	CLK	ADLIB:INBUF	B1	1
	ENOUT	ADLIB:INBUF	J16	1
	LED	ADLIB:OUTBUF	M3	0
	MONITOR[0]	ADLIB:OUTBUF	B5	0
	MONITOR[1]	ADLIB:OUTBUF	C7	Z
	MONITOR[2]	ADLIB:OUTBUF	D9	Z
	MONITOR[3]	ADLIB:OUTBUF	D7	Z
	MONITOR[4]	ADLIB:OUTBUF	A11	Z
	OEa	ADLIB:INBUF	E4	Z
	OEb	ADLIB:INBUF	F1	Z
	OSC_EN	ADLIB:INBUF	K3	Z
	PAD[10]	ADLIB:BIBUF_LVCMOS33U	M8	Z
	PAD[11]	ADLIB:BIBUF_LVCMOS33D	R7	Z
	PAD[12]	ADLIB:BIBUF_LVCMOS33U	D11	Z
	PAD[13]	ADLIB:BIBUF_LVCMOS33D	C12	Z
	PAD[14]	ADLIB:BIBUF_LVCMOS33U	R6	Z

Buttons at the bottom: Load from file..., Save to file..., Show BSR Details (checkbox), Help, OK, Cancel.

**Figure 1-4 • I/O States During Programming Window**

- Click OK to return to the FlashPoint – Programming File Generator window.

**Note:** I/O States During programming are saved to the ADB and resulting programming files after completing programming file generation.

## I/O Power-Up and Supply Voltage Thresholds for Power-On Reset (Commercial and Industrial)

Sophisticated power-up management circuitry is designed into every ProASIC®3 device. These circuits ensure easy transition from the powered-off state to the powered-up state of the device. The many different supplies can power up in any sequence with minimized current spikes or surges.

In addition, the I/O will be in a known state through the power-up sequence. The basic principle is shown in [Figure 2-2 on page 2-5](#).

There are five regions to consider during power-up.

ProASIC3 I/Os are activated only if ALL of the following three conditions are met:

1. VCC and VCCI are above the minimum specified trip points ([Figure 2-2 on page 2-5](#)).
2.  $VCCI > VCC - 0.75 \text{ V}$  (typical)
3. Chip is in the operating mode.

### VCCI Trip Point:

Ramping up:  $0.6 \text{ V} < \text{trip\_point\_up} < 1.2 \text{ V}$

Ramping down:  $0.5 \text{ V} < \text{trip\_point\_down} < 1.1 \text{ V}$

### VCC Trip Point:

Ramping up:  $0.6 \text{ V} < \text{trip\_point\_up} < 1.1 \text{ V}$

Ramping down:  $0.5 \text{ V} < \text{trip\_point\_down} < 1 \text{ V}$

VCC and VCCI ramp-up trip points are about 100 mV higher than ramp-down trip points. This specifically built-in hysteresis prevents undesirable power-up oscillations and current surges. Note the following:

- During programming, I/Os become tristated and weakly pulled up to VCCI.
- JTAG supply, PLL power supplies, and charge pump VPUMP supply have no influence on I/O behavior.

## PLL Behavior at Brownout Condition

Microsemi recommends using monotonic power supplies or voltage regulators to ensure proper power-up behavior. Power ramp-up should be monotonic at least until VCC and VCCPLLX exceed brownout activation levels. The VCC activation level is specified as 1.1 V worst-case (see [Figure 2-2 on page 2-5](#) for more details).

When PLL power supply voltage and/or VCC levels drop below the VCC brownout levels ( $0.75 \text{ V} \pm 0.25 \text{ V}$ ), the PLL output lock signal goes low and/or the output clock is lost. Refer to the "Power-Up/Down Behavior of Low Power Flash Devices" chapter of the [ProASIC3 FPGA Fabric User's Guide](#) for information on clock and lock recovery.

## Internal Power-Up Activation Sequence

1. Core
2. Input buffers

Output buffers, after 200 ns delay from input buffer activation.

## Thermal Characteristics

### Introduction

The temperature variable in the Microsemi Designer software refers to the junction temperature, not the ambient temperature. This is an important distinction because dynamic and static power consumption cause the chip junction to be higher than the ambient temperature.

EQ can be used to calculate junction temperature.

$$T_J = \text{Junction Temperature} = \Delta T + T_A$$

where:

$T_A$  = Ambient Temperature

$\Delta T$  = Temperature gradient between junction (silicon) and ambient  $\Delta T = \theta_{ja} * P$

$\theta_{ja}$  = Junction-to-ambient of the package.  $\theta_{ja}$  numbers are located in [Table 2-5 on page 2-6](#).

P = Power dissipation

**Table 2-15 • Different Components Contributing to the Static Power Consumption in ProASIC3 Devices**

Parameter	Definition	Device Specific Static Power (mW)							
		A3P1000	A3P600	A3P400	A3P250	A3P125	A3P060	A3P030	A3P015
PDC1	Array static power in Active mode	See Table 2-7 on page 2-7.							
PDC2	I/O input pin static power (standard-dependent)	See Table 2-8 on page 2-7 through Table 2-10 on page 2-8.							
PDC3	I/O output pin static power (standard-dependent)	See Table 2-11 on page 2-9 through Table 2-13 on page 2-10.							
PDC4	Static PLL contribution	2.55 mW							
PDC5	Bank quiescent power (VCCI-dependent)	See Table 2-7 on page 2-7.							

**Note:** \*For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi Power spreadsheet calculator or SmartPower tool in Libero SoC software.

## Power Calculation Methodology

This section describes a simplified method to estimate power consumption of an application. For more accurate and detailed power estimations, use the SmartPower tool in Libero SoC software.

The power calculation methodology described below uses the following variables:

- The number of PLLs as well as the number and the frequency of each output clock generated
- The number of combinatorial and sequential cells used in the design
- The internal clock frequencies
- The number and the standard of I/O pins used in the design
- The number of RAM blocks used in the design
- Toggle rates of I/O pins as well as VersaTiles—guidelines are provided in Table 2-16 on page 2-14.
- Enable rates of output buffers—guidelines are provided for typical applications in Table 2-17 on page 2-14.
- Read rate and write rate to the memory—guidelines are provided for typical applications in Table 2-17 on page 2-14. The calculation should be repeated for each clock domain defined in the design.

## Methodology

### Total Power Consumption— $P_{TOTAL}$

$$P_{TOTAL} = P_{STAT} + P_{DYN}$$

$P_{STAT}$  is the total static power consumption.

$P_{DYN}$  is the total dynamic power consumption.

### Total Static Power Consumption— $P_{STAT}$

$$P_{STAT} = P_{DC1} + N_{INPUTS} * P_{DC2} + N_{OUTPUTS} * P_{DC3}$$

$N_{INPUTS}$  is the number of I/O input buffers used in the design.

$N_{OUTPUTS}$  is the number of I/O output buffers used in the design.

### Total Dynamic Power Consumption— $P_{DYN}$

$$P_{DYN} = P_{CLOCK} + P_{S-CELL} + P_{C-CELL} + P_{NET} + P_{INPUTS} + P_{OUTPUTS} + P_{MEMORY} + P_{PLL}$$

### Global Clock Contribution— $P_{CLOCK}$

$$P_{CLOCK} = (P_{AC1} + N_{SPINE} * P_{AC2} + N_{ROW} * P_{AC3} + N_{S-CELL} * P_{AC4}) * F_{CLK}$$

$N_{SPINE}$  is the number of global spines used in the user design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *ProASIC3 FPGA Fabric User's Guide*.

$N_{ROW}$  is the number of VersaTile rows used in the design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *ProASIC3 FPGA Fabric User's Guide*.

**Table 2-42 • 3.3 V LVTTTL / 3.3 V LVCMOS Low Slew**  
**Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case  $V_{CC} = 1.425\text{ V}$ , Worst-Case  $V_{CCI} = 3.0\text{ V}$**   
**Applicable to Advanced I/O Banks**

Drive Strength	Speed Grade	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	$t_{EOUT}$	$t_{ZL}$	$t_{ZH}$	$t_{LZ}$	$t_{HZ}$	$t_{ZLS}$	$t_{ZHS}$	Units
2 mA	Std.	0.66	10.26	0.04	1.02	0.43	10.45	8.90	2.64	2.46	12.68	11.13	ns
	–1	0.56	8.72	0.04	0.86	0.36	8.89	7.57	2.25	2.09	10.79	9.47	ns
	–2	0.49	7.66	0.03	0.76	0.32	7.80	6.64	1.98	1.83	9.47	8.31	ns
4 mA	Std.	0.66	10.26	0.04	1.02	0.43	10.45	8.90	2.64	2.46	12.68	11.13	ns
	–1	0.56	8.72	0.04	0.86	0.36	8.89	7.57	2.25	2.09	10.79	9.47	ns
	–2	0.49	7.66	0.03	0.76	0.32	7.80	6.64	1.98	1.83	9.47	8.31	ns
6 mA	Std.	0.66	7.27	0.04	1.02	0.43	7.41	6.28	2.98	3.04	9.65	8.52	ns
	–1	0.56	6.19	0.04	0.86	0.36	6.30	5.35	2.54	2.59	8.20	7.25	ns
	–2	0.49	5.43	0.03	0.76	0.32	5.53	4.69	2.23	2.27	7.20	6.36	ns
8 mA	Std.	0.66	7.27	0.04	1.02	0.43	7.41	6.28	2.98	3.04	9.65	8.52	ns
	–1	0.56	6.19	0.04	0.86	0.36	6.30	5.35	2.54	2.59	8.20	7.25	ns
	–2	0.49	5.43	0.03	0.76	0.32	5.53	4.69	2.23	2.27	7.20	6.36	ns
12 mA	Std.	0.66	5.58	0.04	1.02	0.43	5.68	4.87	3.21	3.42	7.92	7.11	ns
	–1	0.56	4.75	0.04	0.86	0.36	4.84	4.14	2.73	2.91	6.74	6.05	ns
	–2	0.49	4.17	0.03	0.76	0.32	4.24	3.64	2.39	2.55	5.91	5.31	ns
16 mA	Std.	0.66	5.21	0.04	1.02	0.43	5.30	4.56	3.26	3.51	7.54	6.80	ns
	–1	0.56	4.43	0.04	0.86	0.36	4.51	3.88	2.77	2.99	6.41	5.79	ns
	–2	0.49	3.89	0.03	0.76	0.32	3.96	3.41	2.43	2.62	5.63	5.08	ns
24 mA	Std.	0.66	4.85	0.04	1.02	0.43	4.94	4.54	3.32	3.88	7.18	6.78	ns
	–1	0.56	4.13	0.04	0.86	0.36	4.20	3.87	2.82	3.30	6.10	5.77	ns
	–2	0.49	3.62	0.03	0.76	0.32	3.69	3.39	2.48	2.90	5.36	5.06	ns

**Note:** For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

**Table 2-45 • 3.3 V LVTTTL / 3.3 V LVCMOS High Slew**

 Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Applicable to Standard I/O Banks

Drive Strength	Speed Grade	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	$t_{EOUT}$	$t_{ZL}$	$t_{ZH}$	$t_{LZ}$	$t_{HZ}$	Units
	–2	0.49	3.29	0.03	0.75	0.32	3.36	2.80	1.79	2.01	ns

**Notes:**

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

**Table 2-46 • 3.3 V LVTTTL / 3.3 V LVCMOS Low Slew**

 Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Applicable to Standard I/O Banks

Drive Strength	Speed Grade	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	$t_{EOUT}$	$t_{ZL}$	$t_{ZH}$	$t_{LZ}$	$t_{HZ}$	Units
2 mA	Std.	0.66	9.46	0.04	1.00	0.43	9.64	8.54	2.07	2.04	ns
	–1	0.56	8.05	0.04	0.85	0.36	8.20	7.27	1.76	1.73	ns
	–2	0.49	7.07	0.03	0.75	0.32	7.20	6.38	1.55	1.52	ns
4 mA	Std.	0.66	9.46	0.04	1.00	0.43	9.64	8.54	2.07	2.04	ns
	–1	0.56	8.05	0.04	0.85	0.36	8.20	7.27	1.76	1.73	ns
	–2	0.49	7.07	0.03	0.75	0.32	7.20	6.38	1.55	1.52	ns
6 mA	Std.	0.66	6.57	0.04	1.00	0.43	6.69	5.98	2.40	2.57	ns
	–1	0.56	5.59	0.04	0.85	0.36	5.69	5.09	2.04	2.19	ns
	–2	0.49	4.91	0.03	0.75	0.32	5.00	4.47	1.79	1.92	ns
8 mA	Std.	0.66	6.57	0.04	1.00	0.43	6.69	5.98	2.40	2.57	ns
	–1	0.56	5.59	0.04	0.85	0.36	5.69	5.09	2.04	2.19	ns
	–2	0.49	4.91	0.03	0.75	0.32	5.00	4.47	1.79	1.92	ns

**Note:** For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.



**Table 2-55 • 3.3 V LVTTTL / 3.3 V LVCMOS Low Slew**  
**Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case  $V_{CC} = 1.425\text{ V}$ , Worst-Case  $V_{CCI} = 3.0\text{ V}$**   
**Applicable to Standard I/O Banks**

Drive Strength	Equiv. Software Default Drive Strength Option <sup>1</sup>	Speed Grade	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	$t_{EOUT}$	$t_{ZL}$	$t_{ZH}$	$t_{LZ}$	$t_{HZ}$	Units
100 $\mu\text{A}$	2 mA	Std.	0.60	14.64	0.04	1.52	0.43	14.64	12.97	3.21	3.15	ns
		–1	0.51	12.45	0.04	1.29	0.36	12.45	11.04	2.73	2.68	ns
		–2	0.45	10.93	0.03	1.13	0.32	10.93	9.69	2.39	2.35	ns
100 $\mu\text{A}$	4 mA	Std.	0.60	14.64	0.04	1.52	0.43	14.64	12.97	3.21	3.15	ns
		–1	0.51	12.45	0.04	1.29	0.36	12.45	11.04	2.73	2.68	ns
		–2	0.45	10.93	0.03	1.13	0.32	10.93	9.69	2.39	2.35	ns
100 $\mu\text{A}$	6 mA	Std.	0.60	10.16	0.04	1.52	0.43	10.16	9.08	3.71	3.98	ns
		–1	0.51	8.64	0.04	1.29	0.36	8.64	7.73	3.15	3.39	ns
		–2	0.45	7.58	0.03	1.13	0.32	7.58	6.78	2.77	2.97	ns
100 $\mu\text{A}$	8 mA	Std.	0.60	10.16	0.04	1.52	0.43	10.16	9.08	3.71	3.98	ns
		–1	0.51	8.64	0.04	1.29	0.36	8.64	7.73	3.15	3.39	ns
		–2	0.45	7.58	0.03	1.13	0.32	7.58	6.78	2.77	2.97	ns

**Notes:**

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is  $\pm 100\text{ }\mu\text{A}$ . Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

**Table 2-81 • 1.5 V LVCMOS Low Slew**

Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case  $V_{CC} = 1.425\text{ V}$ , Worst-Case  $V_{CCI} = 1.4\text{ V}$   
 Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	$t_{EOUT}$	$t_{ZL}$	$t_{ZH}$	$t_{LZ}$	$t_{HZ}$	$t_{ZLS}$	$t_{ZHS}$	Units
2 mA	Std.	0.66	12.78	0.04	1.44	0.43	12.81	12.78	3.40	2.64	15.05	15.02	ns
	–1	0.56	10.87	0.04	1.22	0.36	10.90	10.87	2.89	2.25	12.80	12.78	ns
	–2	0.49	9.55	0.03	1.07	0.32	9.57	9.55	2.54	1.97	11.24	11.22	ns
4 mA	Std.	0.66	10.01	0.04	1.44	0.43	10.19	9.55	3.75	3.27	12.43	11.78	ns
	–1	0.56	8.51	0.04	1.22	0.36	8.67	8.12	3.19	2.78	10.57	10.02	ns
	–2	0.49	7.47	0.03	1.07	0.32	7.61	7.13	2.80	2.44	9.28	8.80	ns
6 mA	Std.	0.66	9.33	0.04	1.44	0.43	9.51	8.89	3.83	3.43	11.74	11.13	ns
	–1	0.56	7.94	0.04	1.22	0.36	8.09	7.56	3.26	2.92	9.99	9.47	ns
	–2	0.49	6.97	0.03	1.07	0.32	7.10	6.64	2.86	2.56	8.77	8.31	ns
8 mA	Std.	0.66	8.91	0.04	1.44	0.43	9.07	8.89	3.95	4.05	11.31	11.13	ns
	–1	0.56	7.58	0.04	1.22	0.36	7.72	7.57	3.36	3.44	9.62	9.47	ns
	–2	0.49	6.65	0.03	1.07	0.32	6.78	6.64	2.95	3.02	8.45	8.31	ns
12 mA	Std.	0.66	8.91	0.04	1.44	0.43	9.07	8.89	3.95	4.05	11.31	11.13	ns
	–1	0.56	7.58	0.04	1.22	0.36	7.72	7.57	3.36	3.44	9.62	9.47	ns
	–2	0.49	6.65	0.03	1.07	0.32	6.78	6.64	2.95	3.02	8.45	8.31	ns

**Note:** For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

**Table 2-82 • 1.5 V LVCMOS High Slew**

Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case  $V_{CC} = 1.425\text{ V}$ , Worst-Case  $V_{CCI} = 1.4\text{ V}$   
 Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	$t_{EOUT}$	$t_{ZL}$	$t_{ZH}$	$t_{LZ}$	$t_{HZ}$	$t_{ZLS}$	$t_{ZHS}$	Units
2 mA	Std.	0.66	7.83	0.04	1.42	0.43	6.42	7.83	2.71	2.55	8.65	10.07	ns
	–1	0.56	6.66	0.04	1.21	0.36	5.46	6.66	2.31	2.17	7.36	8.56	ns
	–2	0.49	5.85	0.03	1.06	0.32	4.79	5.85	2.02	1.90	6.46	7.52	ns
4 mA	Std.	0.66	4.84	0.04	1.42	0.43	4.49	4.84	3.03	3.13	6.72	7.08	ns
	–1	0.56	4.12	0.04	1.21	0.36	3.82	4.12	2.58	2.66	5.72	6.02	ns
	–2	0.49	3.61	0.03	1.06	0.32	3.35	3.61	2.26	2.34	5.02	5.28	ns

**Notes:**

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

## Timing Characteristics

**Table 2-88 • 3.3 V PCI/PCI-X**

Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V  
 Applicable to Advanced I/O Banks

Speed Grade	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	$t_{EOUT}$	$t_{ZL}$	$t_{ZH}$	$t_{LZ}$	$t_{HZ}$	$t_{ZLS}$	$t_{ZHS}$	Units
Std.	0.66	2.68	0.04	0.86	0.43	2.73	1.95	3.21	3.58	4.97	4.19	ns
-1	0.56	2.28	0.04	0.73	0.36	2.32	1.66	2.73	3.05	4.22	3.56	ns
-2	0.49	2.00	0.03	0.65	0.32	2.04	1.46	2.40	2.68	3.71	3.13	ns

*Note:* For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

**Table 2-89 • 3.3 V PCI/PCI-X**

Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V  
 Applicable to Standard Plus I/O Banks

Speed Grade	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	$t_{EOUT}$	$t_{ZL}$	$t_{ZH}$	$t_{LZ}$	$t_{HZ}$	$t_{ZLS}$	$t_{ZHS}$	Units
Std.	0.66	2.31	0.04	0.85	0.43	2.35	1.70	2.79	3.22	4.59	3.94	ns
-1	0.56	1.96	0.04	0.72	0.36	2.00	1.45	2.37	2.74	3.90	3.35	ns
-2	0.49	1.72	0.03	0.64	0.32	1.76	1.27	2.08	2.41	3.42	2.94	ns

*Note:* For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

## Differential I/O Characteristics

### Physical Implementation

Configuration of the I/O modules as a differential pair is handled by Microsemi Designer software when the user instantiates a differential I/O macro in the design.

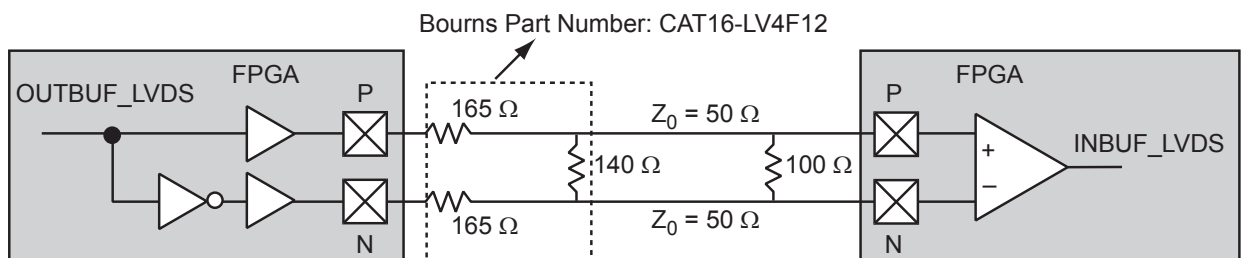
Differential I/Os can also be used in conjunction with the embedded Input Register (InReg), Output Register (OutReg), Enable Register (EnReg), and Double Data Rate (DDR). However, there is no support for bidirectional I/Os or tristates with the LVPECL standards.

### LVDS

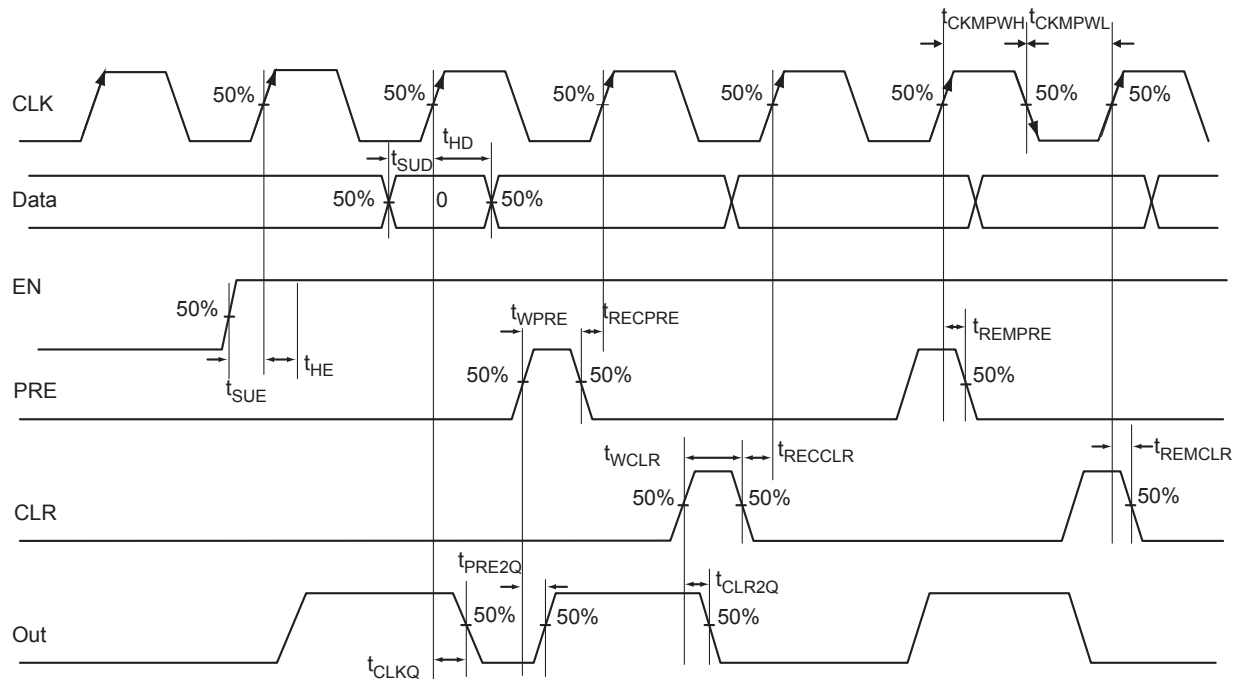
Low-Voltage Differential Signaling (ANSI/TIA/EIA-644) is a high-speed, differential I/O standard. It requires that one data bit be carried through two signal lines, so two pins are needed. It also requires external resistor termination.

The full implementation of the LVDS transmitter and receiver is shown in an example in [Figure 2-12](#). The building blocks of the LVDS transmitter-receiver are one transmitter macro, one receiver macro, three board resistors at the transmitter end, and one resistor at the receiver end. The values for the three driver resistors are different from those used in the LVPECL implementation because the output standard specifications are different.

Along with LVDS I/O, ProASIC3 also supports Bus LVDS structure and Multipoint LVDS (M-LVDS) configuration (up to 40 nodes).



**Figure 2-12 • LVDS Circuit Diagram and Board-Level Implementation**



**Figure 2-27 • Timing Model and Waveforms**

### Timing Characteristics

**Table 2-106 • Register Delays**

Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case  $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2	-1	Std.	Units
$t_{CLKQ}$	Clock-to-Q of the Core Register	0.55	0.63	0.74	ns
$t_{SUD}$	Data Setup Time for the Core Register	0.43	0.49	0.57	ns
$t_{HD}$	Data Hold Time for the Core Register	0.00	0.00	0.00	ns
$t_{SUE}$	Enable Setup Time for the Core Register	0.45	0.52	0.61	ns
$t_{HE}$	Enable Hold Time for the Core Register	0.00	0.00	0.00	ns
$t_{CLR2Q}$	Asynchronous Clear-to-Q of the Core Register	0.40	0.45	0.53	ns
$t_{PRE2Q}$	Asynchronous Preset-to-Q of the Core Register	0.40	0.45	0.53	ns
$t_{REMCLR}$	Asynchronous Clear Removal Time for the Core Register	0.00	0.00	0.00	ns
$t_{RECCLR}$	Asynchronous Clear Recovery Time for the Core Register	0.22	0.25	0.30	ns
$t_{REMPRE}$	Asynchronous Preset Removal Time for the Core Register	0.00	0.00	0.00	ns
$t_{RECPRE}$	Asynchronous Preset Recovery Time for the Core Register	0.22	0.25	0.30	ns
$t_{WCLR}$	Asynchronous Clear Minimum Pulse Width for the Core Register	0.22	0.25	0.30	ns
$t_{WPRE}$	Asynchronous Preset Minimum Pulse Width for the Core Register	0.22	0.25	0.30	ns
$t_{CKMPWH}$	Clock Minimum Pulse Width High for the Core Register	0.32	0.37	0.43	ns
$t_{CKMPWL}$	Clock Minimum Pulse Width Low for the Core Register	0.36	0.41	0.48	ns

**Note:** For specific junction temperature and voltage supply levels, refer to [Table 2-6](#) on [page 2-6](#) for derating values.

**Table 2-121 • A3P250 FIFO 1k×4****Worst Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ ,  $V_{CC} = 1.425\text{ V}$** 

Parameter	Description	–2	–1	Std.	Units
$t_{\text{ENS}}$	REN, WEN Setup Time	4.05	4.61	5.42	ns
$t_{\text{ENH}}$	REN, WEN Hold Time	0.00	0.00	0.00	ns
$t_{\text{BKS}}$	BLK Setup Time	0.19	0.22	0.26	ns
$t_{\text{BKH}}$	BLK Hold Time	0.00	0.00	0.00	ns
$t_{\text{DS}}$	Input Data (WD) Setup Time	0.18	0.21	0.25	ns
$t_{\text{DH}}$	Input Data (WD) Hold Time	0.00	0.00	0.00	ns
$t_{\text{CKQ1}}$	Clock High to New Data Valid on RD (flow-through)	2.36	2.68	3.15	ns
$t_{\text{CKQ2}}$	Clock High to New Data Valid on RD (pipelined)	0.89	1.02	1.20	ns
$t_{\text{RCKEF}}$	RCLK High to Empty Flag Valid	1.72	1.96	2.30	ns
$t_{\text{WCKFF}}$	WCLK High to Full Flag Valid	1.63	1.86	2.18	ns
$t_{\text{CKAF}}$	Clock High to Almost Empty/Full Flag Valid	6.19	7.05	8.29	ns
$t_{\text{RSTFG}}$	RESET Low to Empty/Full Flag Valid	1.69	1.93	2.27	ns
$t_{\text{RSTAF}}$	RESET Low to Almost Empty/Full Flag Valid	6.13	6.98	8.20	ns
$t_{\text{RSTBQ}}$	RESET Low to Data Out Low on RD (flow-through)	0.92	1.05	1.23	ns
	RESET Low to Data Out Low on RD (pipelined)	0.92	1.05	1.23	ns
$t_{\text{REMRSTB}}$	RESET Removal	0.29	0.33	0.38	ns
$t_{\text{RECRSTB}}$	RESET Recovery	1.50	1.71	2.01	ns
$t_{\text{MPWRSTB}}$	RESET Minimum Pulse Width	0.21	0.24	0.29	ns
$t_{\text{CYC}}$	Clock Cycle Time	3.23	3.68	4.32	ns
$F_{\text{MAX}}$	Maximum Frequency for FIFO	310	272	231	MHz

<b>QN132</b>	
<b>Pin Number</b>	<b>A3P125 Function</b>
C17	IO83RSB1
C18	VCCIB1
C19	TCK
C20	VMV1
C21	VPUMP
C22	VJTAG
C23	VCCIB0
C24	NC
C25	NC
C26	GCA1/IO55RSB0
C27	GCC0/IO52RSB0
C28	VCCIB0
C29	IO42RSB0
C30	GNDQ
C31	GBA1/IO40RSB0
C32	GBB0/IO37RSB0
C33	VCC
C34	IO24RSB0
C35	IO19RSB0
C36	IO16RSB0
C37	IO10RSB0
C38	VCCIB0
C39	GAB1/IO03RSB0
C40	VMV0
D1	GND
D2	GND
D3	GND
D4	GND

CS121		CS121		CS121	
Pin Number	A3P060 Function	Pin Number	A3P060 Function	Pin Number	A3P060 Function
A1	GNDQ	D4	IO10RSB0	G7	VCC
A2	IO01RSB0	D5	IO11RSB0	G8	GDC0/IO46RSB0
A3	GAA1/IO03RSB0	D6	IO18RSB0	G9	GDA1/IO49RSB0
A4	GAC1/IO07RSB0	D7	IO32RSB0	G10	GDB0/IO48RSB0
A5	IO15RSB0	D8	IO31RSB0	G11	GCA0/IO40RSB0
A6	IO13RSB0	D9	GCA2/IO41RSB0	H1	IO75RSB1
A7	IO17RSB0	D10	IO30RSB0	H2	IO76RSB1
A8	GBB1/IO22RSB0	D11	IO33RSB0	H3	GFC2/IO78RSB1
A9	GBA1/IO24RSB0	E1	IO87RSB1	H4	GFA2/IO80RSB1
A10	GNDQ	E2	GFC0/IO85RSB1	H5	IO77RSB1
A11	VMV0	E3	IO92RSB1	H6	GEC2/IO66RSB1
B1	GAA2/IO95RSB1	E4	IO94RSB1	H7	IO54RSB1
B2	IO00RSB0	E5	VCC	H8	GDC2/IO53RSB1
B3	GAA0/IO02RSB0	E6	VCCIB0	H9	VJTAG
B4	GAC0/IO06RSB0	E7	GND	H10	TRST
B5	IO08RSB0	E8	GCC0/IO36RSB0	H11	IO44RSB0
B6	IO12RSB0	E9	IO34RSB0	J1	GEC1/IO74RSB1
B7	IO16RSB0	E10	GCB1/IO37RSB0	J2	GEC0/IO73RSB1
B8	GBC1/IO20RSB0	E11	GCC1/IO35RSB0	J3	GEB1/IO72RSB1
B9	GBB0/IO21RSB0	F1	VCOMPLF	J4	GEA0/IO69RSB1
B10	GBB2/IO27RSB0	F2	GFB0/IO83RSB1	J5	GEB2/IO67RSB1
B11	GBA2/IO25RSB0	F3	GFA0/IO82RSB1	J6	IO62RSB1
C1	IO89RSB1	F4	GFC1/IO86RSB1	J7	GDA2/IO51RSB1
C2	GAC2/IO91RSB1	F5	VCCIB1	J8	GDB2/IO52RSB1
C3	GAB1/IO05RSB0	F6	VCC	J9	TDI
C4	GAB0/IO04RSB0	F7	VCCIB0	J10	TDO
C5	IO09RSB0	F8	GCB2/IO42RSB0	J11	GDC1/IO45RSB0
C6	IO14RSB0	F9	GCC2/IO43RSB0	K1	GEB0/IO71RSB1
C7	GBA0/IO23RSB0	F10	GCB0/IO38RSB0	K2	GEA1/IO70RSB1
C8	GBC0/IO19RSB0	F11	GCA1/IO39RSB0	K3	GEA2/IO68RSB1
C9	IO26RSB0	G1	VCCPLF	K4	IO64RSB1
C10	IO28RSB0	G2	GFB2/IO79RSB1	K5	IO60RSB1
C11	GBC2/IO29RSB0	G3	GFA1/IO81RSB1	K6	IO59RSB1
D1	IO88RSB1	G4	GFB1/IO84RSB1	K7	IO56RSB1
D2	IO90RSB1	G5	GND	K8	TCK
D3	GAB2/IO93RSB1	G6	VCCIB1	K9	TMS

TQ144	
Pin Number	A3P060 Function
1	GAA2/IO51RSB1
2	IO52RSB1
3	GAB2/IO53RSB1
4	IO95RSB1
5	GAC2/IO94RSB1
6	IO93RSB1
7	IO92RSB1
8	IO91RSB1
9	VCC
10	GND
11	VCCIB1
12	IO90RSB1
13	GFC1/IO89RSB1
14	GFC0/IO88RSB1
15	GFB1/IO87RSB1
16	GFB0/IO86RSB1
17	VCOMPLF
18	GFA0/IO85RSB1
19	VCCPLF
20	GFA1/IO84RSB1
21	GFA2/IO83RSB1
22	GFB2/IO82RSB1
23	GFC2/IO81RSB1
24	IO80RSB1
25	IO79RSB1
26	IO78RSB1
27	GND
28	VCCIB1
29	GEC1/IO77RSB1
30	GEC0/IO76RSB1
31	GEB1/IO75RSB1
32	GEB0/IO74RSB1
33	GEA1/IO73RSB1
34	GEA0/IO72RSB1
35	VMV1
36	GNDQ

TQ144	
Pin Number	A3P060 Function
37	NC
38	GEA2/IO71RSB1
39	GEB2/IO70RSB1
40	GEC2/IO69RSB1
41	IO68RSB1
42	IO67RSB1
43	IO66RSB1
44	IO65RSB1
45	VCC
46	GND
47	VCCIB1
48	NC
49	IO64RSB1
50	NC
51	IO63RSB1
52	NC
53	IO62RSB1
54	NC
55	IO61RSB1
56	NC
57	NC
58	IO60RSB1
59	IO59RSB1
60	IO58RSB1
61	IO57RSB1
62	NC
63	GND
64	NC
65	GDC2/IO56RSB1
66	GDB2/IO55RSB1
67	GDA2/IO54RSB1
68	GNDQ
69	TCK
70	TDI
71	TMS
72	VMV1

TQ144	
Pin Number	A3P060 Function
73	VPUMP
74	NC
75	TDO
76	TRST
77	VJTAG
78	GDA0/IO50RSB0
79	GDB0/IO48RSB0
80	GDB1/IO47RSB0
81	VCCIB0
82	GND
83	IO44RSB0
84	GCC2/IO43RSB0
85	GCB2/IO42RSB0
86	GCA2/IO41RSB0
87	GCA0/IO40RSB0
88	GCA1/IO39RSB0
89	GCB0/IO38RSB0
90	GCB1/IO37RSB0
91	GCC0/IO36RSB0
92	GCC1/IO35RSB0
93	IO34RSB0
94	IO33RSB0
95	NC
96	NC
97	NC
98	VCCIB0
99	GND
100	VCC
101	IO30RSB0
102	GBC2/IO29RSB0
103	IO28RSB0
104	GBB2/IO27RSB0
105	IO26RSB0
106	GBA2/IO25RSB0
107	VMV0
108	GNDQ



FG484	
Pin Number	A3P400 Function
E21	NC
E22	NC
F1	NC
F2	NC
F3	NC
F4	IO154VDB3
F5	IO155VDB3
F6	IO11RSB0
F7	IO07RSB0
F8	GAC0/IO04RSB0
F9	GAC1/IO05RSB0
F10	IO20RSB0
F11	IO24RSB0
F12	IO33RSB0
F13	IO39RSB0
F14	IO45RSB0
F15	GBC0/IO54RSB0
F16	IO48RSB0
F17	VMV0
F18	IO61NPB1
F19	IO63PDB1
F20	NC
F21	NC
F22	NC
G1	NC
G2	NC
G3	NC
G4	IO151VDB3
G5	IO151UDB3
G6	GAC2/IO153UDB3
G7	IO06RSB0
G8	GNDQ
G9	IO10RSB0
G10	IO19RSB0
G11	IO26RSB0
G12	IO30RSB0

FG484	
Pin Number	A3P400 Function
G13	IO40RSB0
G14	IO46RSB0
G15	GNDQ
G16	IO47RSB0
G17	GBB2/IO61PPB1
G18	IO53RSB0
G19	IO63NDB1
G20	NC
G21	NC
G22	NC
H1	NC
H2	NC
H3	VCC
H4	IO150PDB3
H5	IO08RSB0
H6	IO153VDB3
H7	IO152VDB3
H8	VMV0
H9	VCCIB0
H10	VCCIB0
H11	IO25RSB0
H12	IO31RSB0
H13	VCCIB0
H14	VCCIB0
H15	VMV1
H16	GBC2/IO62PDB1
H17	IO65RSB1
H18	IO52RSB0
H19	IO66PDB1
H20	VCC
H21	NC
H22	NC
J1	NC
J2	NC
J3	NC
J4	IO150NDB3

FG484	
Pin Number	A3P400 Function
J5	IO149NPB3
J6	IO09RSB0
J7	IO152UDB3
J8	VCCIB3
J9	GND
J10	VCC
J11	VCC
J12	VCC
J13	VCC
J14	GND
J15	VCCIB1
J16	IO62NDB1
J17	IO49RSB0
J18	IO64PPB1
J19	IO66NDB1
J20	NC
J21	NC
J22	NC
K1	NC
K2	NC
K3	NC
K4	IO148NDB3
K5	IO148PDB3
K6	IO149PPB3
K7	GFC1/IO147PPB3
K8	VCCIB3
K9	VCC
K10	GND
K11	GND
K12	GND
K13	GND
K14	VCC
K15	VCCIB1
K16	GCC1/IO67PPB1
K17	IO64NPB1
K18	IO73PDB1

FG484	
Pin Number	A3P1000 Function
R17	GDB1/IO112PPB1
R18	GDC1/IO111PDB1
R19	IO107NDB1
R20	VCC
R21	IO104NDB1
R22	IO105PDB1
T1	IO198PDB3
T2	IO198NDB3
T3	NC
T4	IO194PPB3
T5	IO192PPB3
T6	GEC1/IO190PPB3
T7	IO192NPB3
T8	GNDQ
T9	GEA2/IO187RSB2
T10	IO161RSB2
T11	IO155RSB2
T12	IO141RSB2
T13	IO129RSB2
T14	IO124RSB2
T15	GNDQ
T16	IO110PDB1
T17	VJTAG
T18	GDC0/IO111NDB1
T19	GDA1/IO113PDB1
T20	NC
T21	IO108PDB1
T22	IO105NDB1
U1	IO195PDB3
U2	IO195NDB3
U3	IO194NPB3
U4	GEB1/IO189PDB3
U5	GEB0/IO189NDB3
U6	VMV2
U7	IO179RSB2
U8	IO171RSB2

FG484	
Pin Number	A3P1000 Function
U9	IO165RSB2
U10	IO159RSB2
U11	IO151RSB2
U12	IO137RSB2
U13	IO134RSB2
U14	IO128RSB2
U15	VMV1
U16	TCK
U17	VPUMP
U18	TRST
U19	GDA0/IO113NDB1
U20	NC
U21	IO108NDB1
U22	IO109PDB1
V1	NC
V2	NC
V3	GND
V4	GEA1/IO188PDB3
V5	GEA0/IO188NDB3
V6	IO184RSB2
V7	GEC2/IO185RSB2
V8	IO168RSB2
V9	IO163RSB2
V10	IO157RSB2
V11	IO149RSB2
V12	IO143RSB2
V13	IO138RSB2
V14	IO131RSB2
V15	IO125RSB2
V16	GDB2/IO115RSB2
V17	TDI
V18	GNDQ
V19	TDO
V20	GND
V21	NC
V22	IO109NDB1

FG484	
Pin Number	A3P1000 Function
W1	NC
W2	IO191PDB3
W3	NC
W4	GND
W5	IO183RSB2
W6	GEB2/IO186RSB2
W7	IO172RSB2
W8	IO170RSB2
W9	IO164RSB2
W10	IO158RSB2
W11	IO153RSB2
W12	IO142RSB2
W13	IO135RSB2
W14	IO130RSB2
W15	GDC2/IO116RSB2
W16	IO120RSB2
W17	GDA2/IO114RSB2
W18	TMS
W19	GND
W20	NC
W21	NC
W22	NC
Y1	VCCIB3
Y2	IO191NDB3
Y3	NC
Y4	IO182RSB2
Y5	GND
Y6	IO177RSB2
Y7	IO174RSB2
Y8	VCC
Y9	VCC
Y10	IO154RSB2
Y11	IO148RSB2
Y12	IO140RSB2
Y13	NC
Y14	VCC

Revision	Changes	Page
Revision 13 (January 2013)	The "ProASIC3 Ordering Information" section has been updated to mention "Y" as "Blank" mentioning "Device Does Not Include License to Implement IP Based on the Cryptography Research, Inc. (CRI) Patent Portfolio" (SAR 43104).	1-IV
	Added a note to Table 2-2 • Recommended Operating Conditions 1 (SAR 43644): The programming temperature range supported is $T_{\text{ambient}} = 0^{\circ}\text{C}$ to $85^{\circ}\text{C}$ .	2-2
	The note in Table 2-115 • ProASIC3 CCC/PLL Specification referring the reader to SmartGen was revised to refer instead to the online help associated with the core (SAR 42569).	2-90
	Libero Integrated Design Environment (IDE) was changed to Libero System-on-Chip (SoC) throughout the document (SAR 40284). Live at Power-Up (LAPU) has been replaced with 'Instant On'.	NA
Revision 12 (September 2012)	The Security section was modified to clarify that Microsemi does not support read-back of programmed data.	1-1
	Added a Note stating "VMV pins must be connected to the corresponding VCCI pins. See the "VMVx I/O Supply Voltage (quiet)" section on page 3-1 for further information" to Table 2-1 • Absolute Maximum Ratings and Table 2-2 • Recommended Operating Conditions 1 (SAR 38321).	2-1 2-2
	Table 2-35 • Duration of Short Circuit Event Before Failure was revised to change the maximum temperature from $110^{\circ}\text{C}$ to $100^{\circ}\text{C}$ , with an example of six months instead of three months (SAR 37933).	2-31
	In Table 2-93 • Minimum and Maximum DC Input and Output Levels, VIL and VIH were revised so that the maximum is 3.6 V for all listed values of VCCI (SAR 28549).	2-68
	Figure 2-37 • FIFO Read and Figure 2-38 • FIFO Write are new (SAR 28371).	2-99
	The following sentence was removed from the "VMVx I/O Supply Voltage (quiet)" section in the "Pin Descriptions" chapter: "Within the package, the VMV plane is decoupled from the simultaneous switching noise originating from the output buffer VCCI domain" and replaced with "Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks" (SAR 38321). The datasheet mentions that "VMV pins must be connected to the corresponding VCCI pins" for an ESD enhancement.	3-1

Revision	Changes	Page
<b>Revision 2 (cont'd)</b>	The "ProASIC3 FPGAs Package Sizes Dimensions" table is new.	III
	In the "ProASIC3 Ordering Information", the QN package measurements were updated to include both 0.4 mm and 0.5 mm.	IV
	In the General Description section the number of I/Os was updated from 288 to 300.	1-1
	The "QN68 – Bottom View" section is new.	4-3
Packaging v1.2		
<b>Revision 1 (Feb 2008)</b> DC and Switching Characteristics v1.1	In Table 2-2 • Recommended Operating Conditions 1, $T_J$ was listed in the symbol column and was incorrect. It was corrected and changed to $T_A$ .	2-2
	In Table 2-3 • Flash Programming Limits – Retention, Storage and Operating Temperature, Maximum Operating Junction Temperature was changed from 110°C to 100°C for both commercial and industrial grades.	2-3
	The "PLL Behavior at Brownout Condition" section is new.	2-4
	In the "PLL Contribution—PPLL" section, the following was deleted: FCLKIN is the input clock frequency.	2-14
	In Table 2-21 • Summary of Maximum and Minimum DC Input Levels, the note was incorrect. It previously said $T_J$ and it was corrected and changed to $T_A$ .	2-21
	In Table 2-115 • ProASIC3 CCC/PLL Specification, the SCLK parameter and note 1 are new.	2-90
	Table 2-125 • JTAG 1532 was populated with the parameter data, which was not in the previous version of the document.	2-108
	In the "VQ100" A3P030 pin table, the function of pin 63 was incorrect and changed from IO39RSB0 to GDB0/IO38RSB0.	4-19
Packaging v1.1		
<b>Revision 0 (Jan 2008)</b>	This document was previously in datasheet v2.2. As a result of moving to the handbook format, Actel has restarted the version numbers.	N/A
v2.2 (July 2007)	The M7 and M1 device part numbers have been updated in Table 1 • ProASIC3 Product Family, "I/Os Per Package", "Automotive ProASIC3 Ordering Information", "Temperature Grade Offerings", and "Speed Grade and Temperature Grade Matrix".	i, ii, iii, iii, iv
	The words "ambient temperature" were added to the temperature range in the "Automotive ProASIC3 Ordering Information", "Temperature Grade Offerings", and "Speed Grade and Temperature Grade Matrix" sections.	iii, iv
	The $T_J$ parameter in Table 3-2 • Recommended Operating Conditions was changed to $T_A$ , ambient temperature, and table notes 4–6 were added.	3-2
v2.1 (May 2007)	In the "Clock Conditioning Circuit (CCC) and PLL" section, the Wide Input Frequency Range (1.5 MHz to 200 MHz) was changed to (1.5 MHz to 350 MHz).	i
	The "Clock Conditioning Circuit (CCC) and PLL" section was updated.	i
	In the "I/Os Per Package" section, the A3P030, A3P060, A3P125, ACP250, and A3P600 device I/Os were updated.	ii
	Table 3-5 • Package Thermal Resistivities was updated with A3P1000 information. The note below the table is also new.	3-5

Revision	Changes	Page
Advance v0.6 (continued)	The "RESET" section was updated.	2-25
	The "WCLK and RCLK" section was updated.	2-25
	The "RESET" section was updated.	2-25
	The "RESET" section was updated.	2-27
	The "Introduction" of the "Advanced I/Os" section was updated.	2-28
	The "I/O Banks" section is new. This section explains the following types of I/Os: Advanced Standard+ Standard  Table 2-12 • Automotive ProASIC3 Bank Types Definition and Differences is new. This table describes the standards listed above.	2-29
	PCI-X 3.3 V was added to the Compatible Standards for 3.3 V in Table 2-11 • VCCI Voltages and Compatible Standards	2-29
	Table 2-13 • ProASIC3 I/O Features was updated.	2-30
	The "Double Data Rate (DDR) Support" section was updated to include information concerning implementation of the feature.	2-32
	The "Electrostatic Discharge (ESD) Protection" section was updated to include testing information.	2-35
	Level 3 and 4 descriptions were updated in Table 2-43 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in ProASIC3 Devices.	2-64
	The notes in Table 2-43 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in ProASIC3 Devices were updated.	2-64
	The "Simultaneous Switching Outputs (SSOs) and Printed Circuit Board Layout" section is new.	2-41
	A footnote was added to Table 2-14 • Maximum I/O Frequency for Single-Ended and Differential I/Os in All Banks in Automotive ProASIC3 Devices (maximum drive strength and high slew selected).	2-30
	Table 2-18 • Automotive ProASIC3 I/O Attributes vs. I/O Standard Applications	2-45
	Table 2-50 • ProASIC3 Output Drive (OUT_DRIVE) for Standard I/O Bank Type (A3P030 device)	2-83
	Table 2-51 • ProASIC3 Output Drive for Standard+ I/O Bank Type was updated.	2-84
	Table 2-54 • ProASIC3 Output Drive for Advanced I/O Bank Type was updated.	2-84
	The "x" was updated in the "User I/O Naming Convention" section.	2-48
	The "VCC Core Supply Voltage" pin description was updated.	2-50
	The "VMVx I/O Supply Voltage (quiet)" pin description was updated to include information concerning leaving the pin unconnected.	2-50
	The "VJTAG JTAG Supply Voltage" pin description was updated.	2-50
	The "VPUMP Programming Supply Voltage" pin description was updated to include information on what happens when the pin is tied to ground.	2-50
	The "I/O User Input/Output" pin description was updated to include information on what happens when the pin is unused.	2-50
	The "JTAG Pins" section was updated to include information on what happens when the pin is unused.	2-51